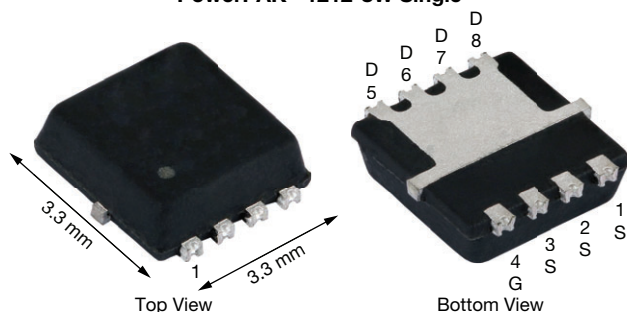


Automotive P-Channel 100 V (D-S) 175 °C MOSFET

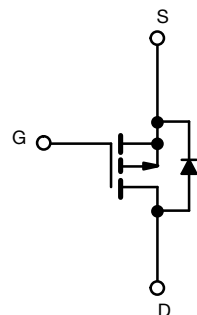
PowerPAK® 1212-8W Single

Marking code: Q064

PRODUCT SUMMARY

V_{DS} (V)	-100
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0800
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.1100
I_D (A)	-16
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE


P-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK 1212-8W
Lead (Pb)-free and halogen-free	SQS201CENW (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-100	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	$T_C = 25$ °C ^a	A
		$T_C = 125$ °C	
Continuous source current (diode conduction) ^a	I_S	-16	
Pulsed drain current ^b	I_{DM}	-46	
Single pulse avalanche current	I_{AS}	-22	
Single pulse avalanche energy	E_{AS}	24.2	mJ
Maximum power dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 125$ °C	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	81	°C/W
Junction-to-case (drain)	R_{thJC}	2.4	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK1212-8W package may have visible exposed Cu at the end of the lead terminals due to the singulation process. However, the leads also have plated indents on the top and bottom surfaces that promote the formation of a solder fillet compatible with automated optical inspection methods
- Rework conditions: manual soldering with a soldering iron is not recommended

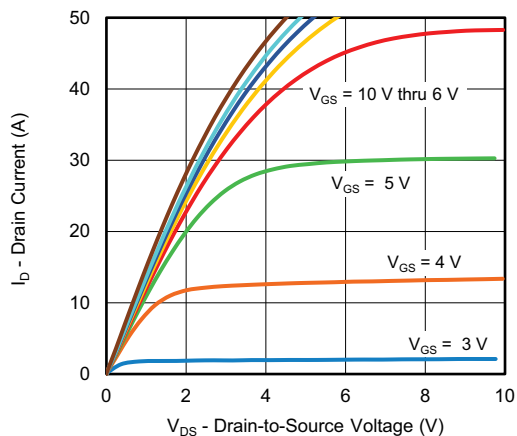
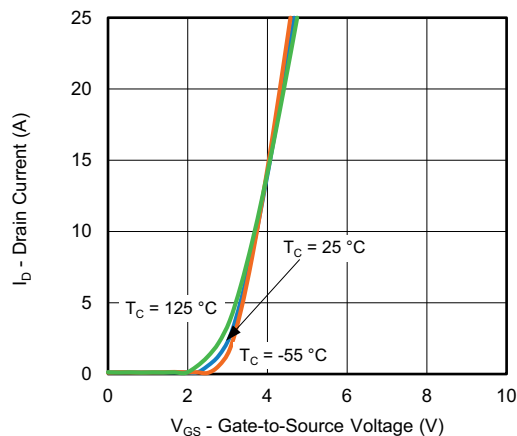
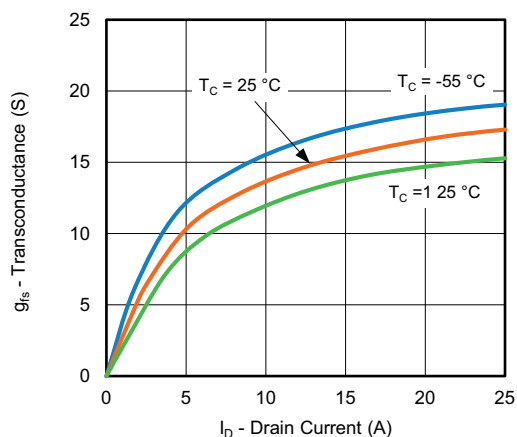
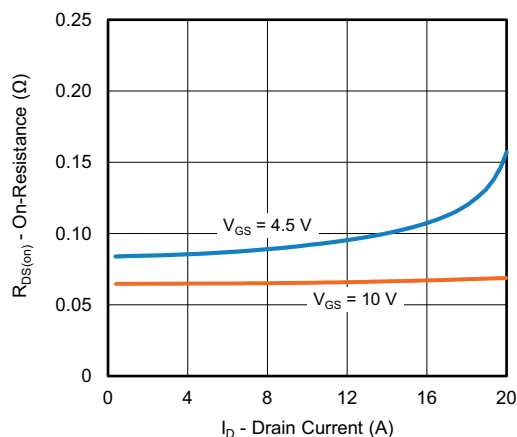
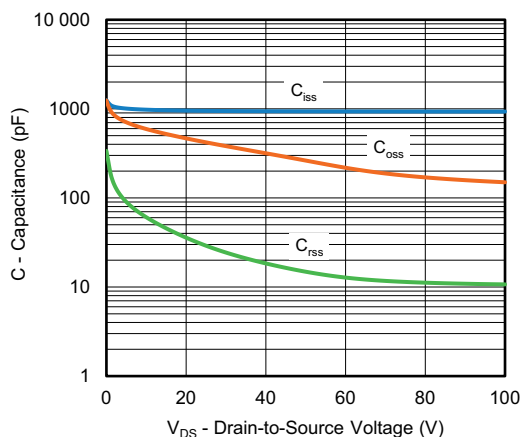
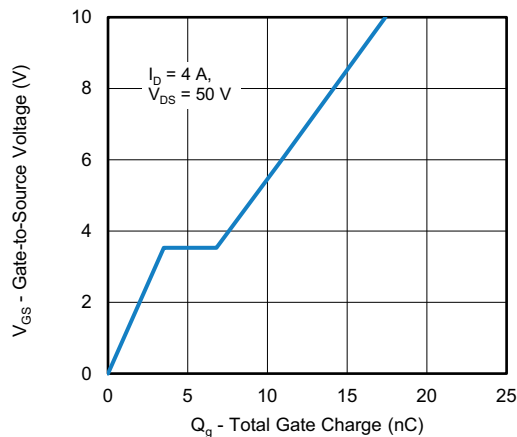


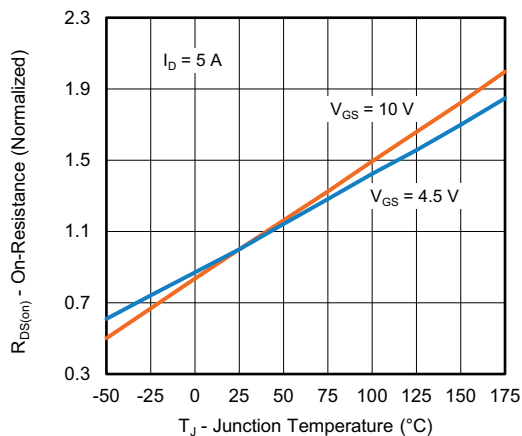
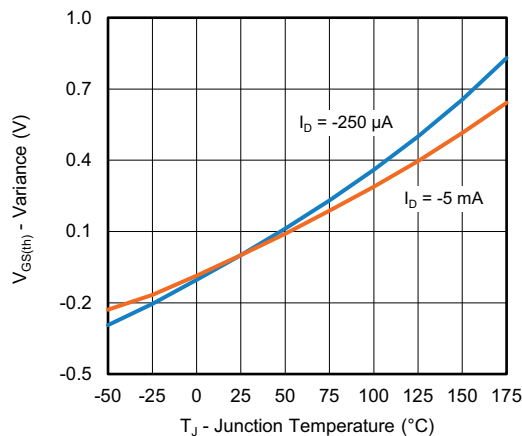
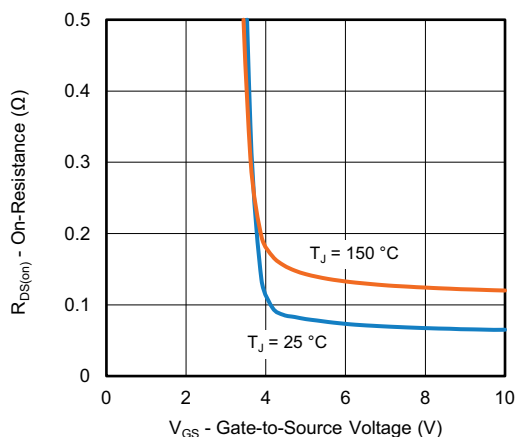
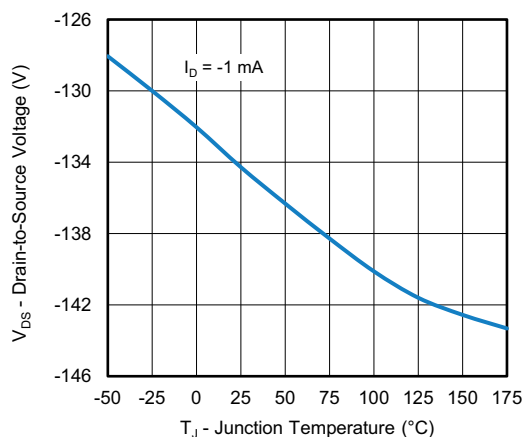
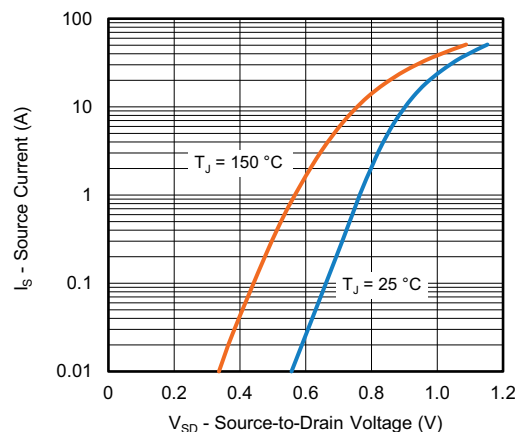
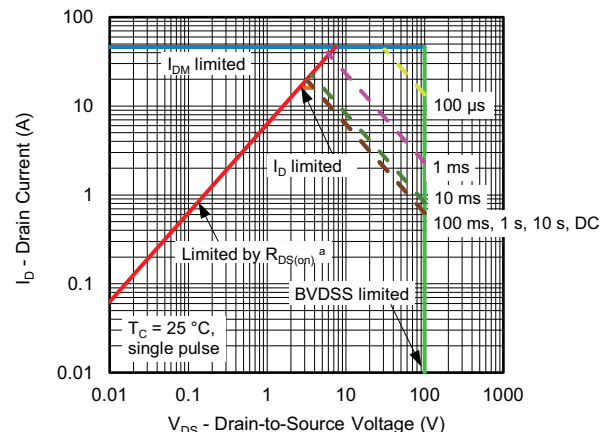
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-100	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-2.0	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -100 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -100 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -100 V, T _J = 175 °C	-	-	-200	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≥ -5 V	-10	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -6 A	-	0.0650	0.0800	Ω
		V _{GS} = -10 V	I _D = -6 A, T _J = 125 °C	-	-	0.1330	
		V _{GS} = -10 V	I _D = -6 A, T _J = 175 °C	-	-	0.1600	
		V _{GS} = -4.5 V	I _D = -4 A	-	0.0860	0.1100	
Forward transconductance ^b	g _{fs}	V _{DS} = -15 V, I _D = -6 A		-	12	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	949	1330	pF
Output capacitance	C _{OSS}			-	421	590	
Reverse transfer capacitance	C _{rss}			-	30	42	
Total gate charge ^c	Q _g	V _{GS} = -10 V	V _{DS} = -50 V, I _D = -4 A	-	17.4	26	nC
Gate-source charge ^c	Q _{gs}			-	3.5	-	
Gate-drain charge ^c	Q _{gd}			-	3.3	-	
Gate resistance	R _g	f = 1 MHz		4.9	9.82	14.8	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = -50 V, R _L = 12.5 Ω I _D ≡ -4 A, V _{GEN} = -10 V, R _g = 1 Ω		-	9	14	ns
Rise time ^c	t _r			-	4	7	
Turn-off delay time ^c	t _{d(off)}			-	30	45	
Fall time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Characteristic ^b							
Pulsed current ^a	I _{SM}			-	-	-46	A
Forward voltage	V _{SD}	I _F = -6 A, V _{GS} = 0 V		-	-0.86	-1.1	V
Body diode reverse recovery time	t _{rr}	I _F = -5 A, di/dt = 100 A/μs		-	45	90	ns
Body diode reverse recovery charge	Q _{rr}			-	105	210	nC
Reverse recovery fall time	t _a			-	39	-	ns
Reverse recovery rise time	t _b			-	6	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-4.89	-	A

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

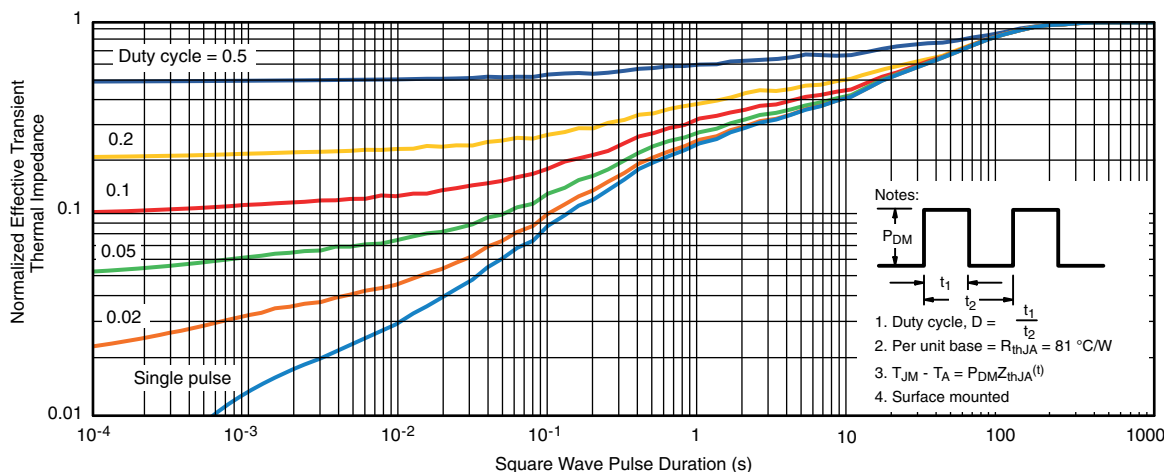
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Drain Source Breakdown vs. Junction Temperature

Source Drain Diode Forward Voltage

Safe Operating Area
Note

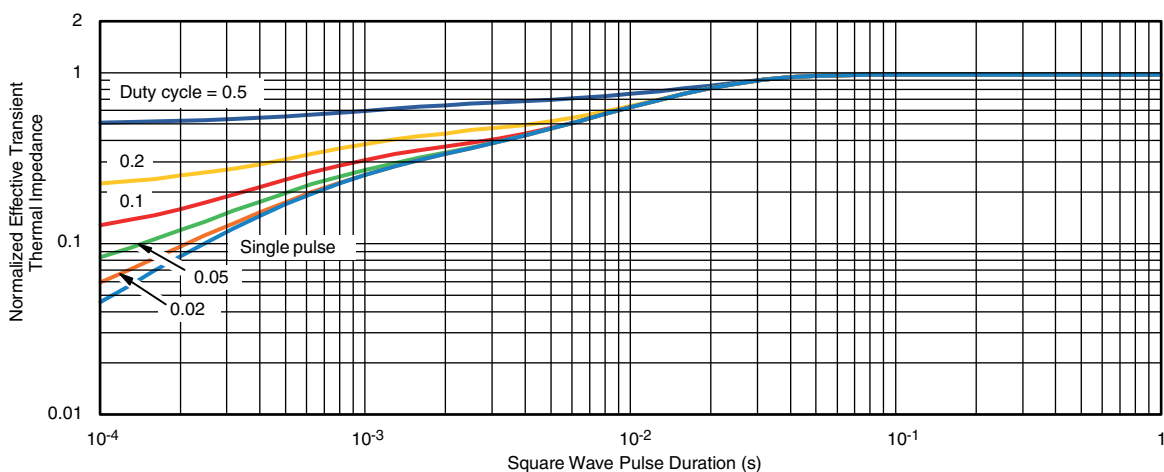
- $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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